

Schottky Barrier Rectifiers

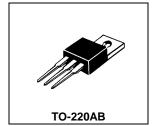
Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

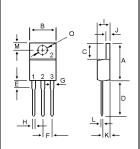
- * Low Forward Voltage.
- * Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- *Low Power Loss & High efficiency.
- * 150 Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory

Flammability Classification 94V-O

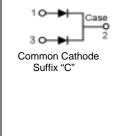
SCHOTTKY BARRIER RECTIFIERS

20 AMPERES 150 VOLTS





DIM	MILLIMETERS		
וווע	MIN	MAX	
Α	14.68	15.32	
В	9.78	10.42	
С	5.02	6.52	
D	13.06	14.62	
Е	3.57	4.07	
F	2.42	2.66	
G	1.12	1.36	
Н	0.72	0.96	
- 1	4.22	4.98	
J	1.14	1.38	
K	2.20	2.98	
L	0.33	0.55	
М	2.48	2.98	
0	3.70	3.90	



MAXIMUM RATINGS

Characteristic	Symbol	S20C150C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	150	V
RMS Reverse Voltage	V _{R(RMS)}	105	V
Average Rectifier Forward Current Total Device (Rated V _R), T _C =100	I _{F(AV)}	10 20	А
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	20	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	150	А
Operating and Storage Junction Temperature Range	T_J , T_stg	-65 to +150	

ELECTRIAL CHARACTERISTICS

Characteristic	Symbol	S20C150C	Unit
Maximum Instantaneous Forward Voltage ($I_F = 10 \text{ Amp } T_C = 25$) ($I_F = 10 \text{ Amp } T_C = 125$)	V _F	0.95 0.85	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25$) (Rated DC Voltage, $T_C = 125$)	I _R	0.5 20	mA

